



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _A = +25°C
-30V	$90m\Omega @ V_{GS} = -10V$	-3.3A
-307	134mΩ @ $V_{GS} = -4.5V$	-2.5A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions

Features

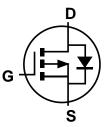
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

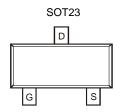
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)



Top View



Internal Schematic



Top View

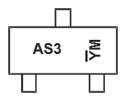
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3165L-7	SOT23	3000/Tape & Reel
DMP3165L-13	SOT23	10000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



AS3 = Product Type Marking Code $\overline{Y}M$ = Date Code Marking \overline{Y} = Year (ex: F = 2018) M = Month (ex: 9 = September)

Date Code Key

Year	2017	2018	20	019	2020	2021	I	2022		2023	202	24	2025
Code	Е	F		G	Н	1		J		K	L		M
Month	Jan	Feb	Mar	Apr	May	Jun	Ju	ıl A	ug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	'	8	9	0	N	D



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Character	istic		Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			V _{GSS}	±20	V
Drain Current (Note 6) V _{GS} = -10V	$T_A = +25$ °C $T_A = +70$ °C	I _D	-3.3 -2.7	А	
Pulsed Drain Current (380µs Pulse, D	outy Cycle = 19	%)	I _{DM}	-13	А

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		P_{D}	0.8	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ heta JA}$	159	°C/W	
Total Power Dissipation (Note 6)		P _D	1.3	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ heta JA}$	98	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

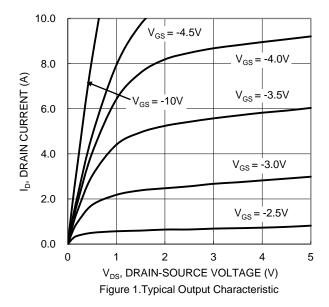
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

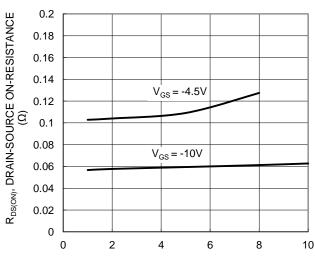
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-800	nA	$V_{DS} = -30V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±80 ±800	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$ $V_{GS} = \pm 15V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-1.3	_	-2.1	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$
Static Drain-Source On-Resistance	D		59	90	mΩ	$V_{GS} = -10V, I_D = -2.7A$
Static Diam-Source On-Nesistance	R _{DS(ON)}	_	100	134	11122	$V_{GS} = -4.5V$, $I_{D} = -2.0A$
Diode Forward Voltage	V _{SD}	_	-0.83	-1.26	V	$V_{GS} = 0V$, $I_{S} = -2.7A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	_	300		pF	.,
Output Capacitance	Coss	_	52		pF	$V_{DS} = -10V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	35		pF	1 - 1.000112
Gate Resistance	R _G	_	12.5		Ω	$V_{GS} = 0V$, $V_{DS} = 0V$, $f = 1.0MHz$
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	1.0	_	nC	
Total Gate Charge (V _{GS} = -10V)	Qg	_	2.0		nC	$V_{GS} = -10V/-4.5V$,
Gate-Source Charge	Qgs	_	0.2		nC	$V_{DS} = -15V, I_{D} = -3A$
Gate-Drain Charge	Q _{gd}	_	0.5	_	nC	
Turn-On Delay Time	t _{D(ON)}	_	3.7		ns	
Turn-On Rise Time	t _R	_	5.5		ns	$V_{DS} = -15V, V_{GS} = -10V,$
Turn-Off Delay Time	t _{D(OFF)}	_	13.6	_	ns	$R_G = 6\Omega$, $I_D = -1A$
Turn-Off Fall Time	t _F	_	8.4		ns	
Reverse Recovery Time	t _{RR}	_	6.5		ns	$I_F = -1.0A$, $di/dt = 100A/\mu s$
Reverse Recovery Charge	Q _{RR}	_	1.2	_	nC	$I_F = -1.0A$, $di/dt = 100A/\mu s$

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect. Notes:

^{8.} Guaranteed by design. Not subject to product testing.







I_D, DRAIN-SOURCE CURRENT (A) Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

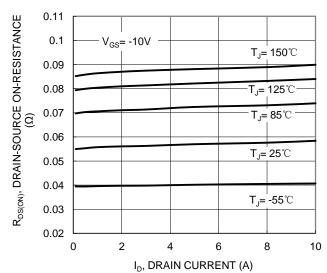
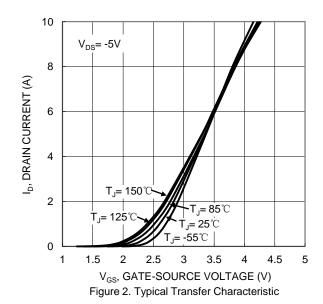
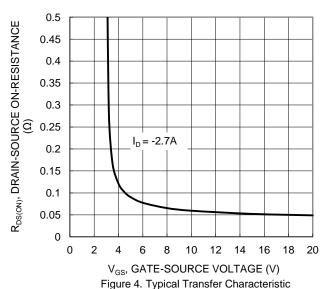


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





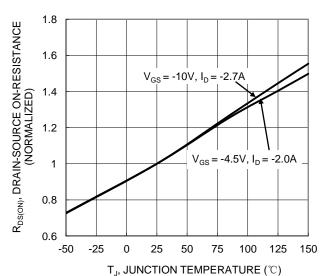


Figure 6. On-Resistance Variation with Temperature



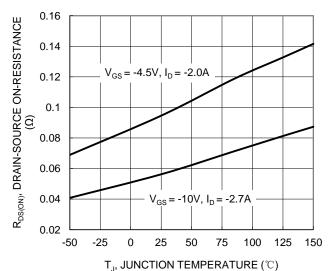


Figure 7. On-Resistance Variation with Temperature

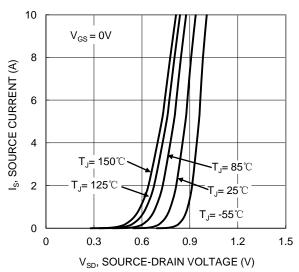


Figure 9. Diode Forward Voltage vs. Current

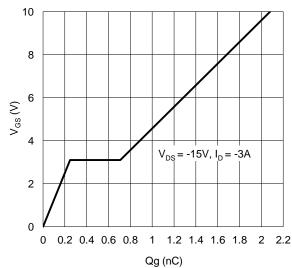
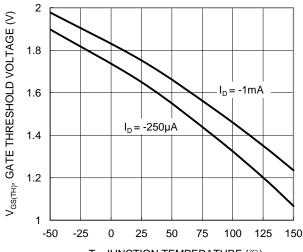


Figure 11. Gate Charge



T_J, JUNCTION TEMPERATURE (℃) Figure 8. Gate Threshold Variation vs. JunctionTemperature

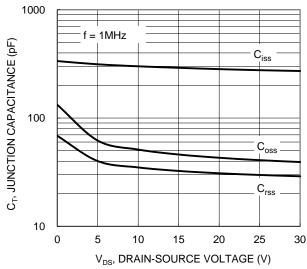


Figure 10. Typical Junction Capacitance

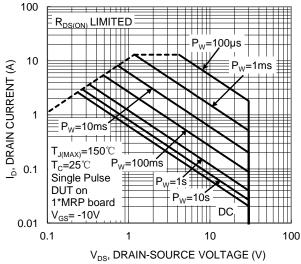


Figure 12. SOA, Safe Operation Area



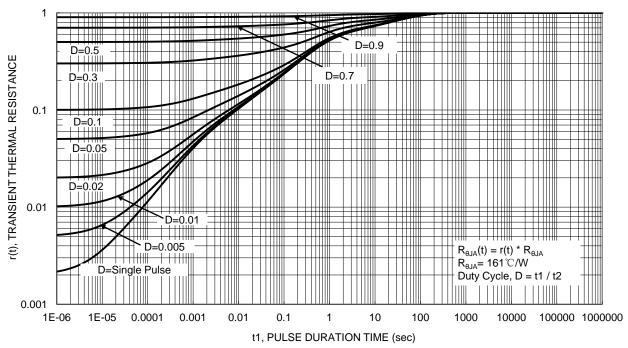


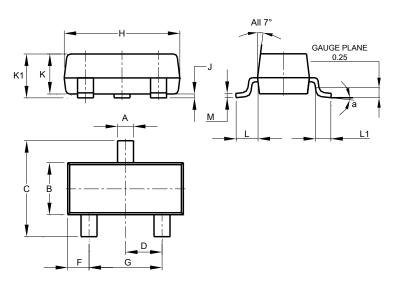
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

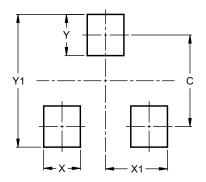


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	0°	8°				
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)			
С	2.0			
Х	0.8			
X1	1.35			
Y	0.9			
Y1	2.9			



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